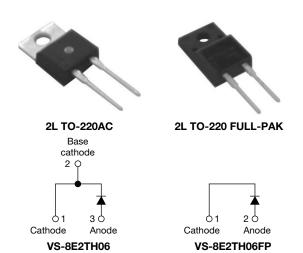
Vishay Semiconductors

RoHS

COMPLIANT

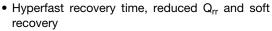
HALOGEN FREE

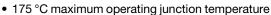
Hyperfast Rectifier, 8 A FRED Pt®



PRODUCT SUMMARY				
Package	2L TO-220AC, 2L TO-220 FP			
I _{F(AV)}	8 A			
V _R	600 V			
V _F at I _F	2.5 V			
t _{rr} (typ.)	17 ns			
T _J max.	175 °C			
Diode variation	Single die			

FEATURES







• True 2 pin package

· Low forward voltage drop

Low leakage current

• Fully isolated package (V_{INS} = 2500 V_{RMS})

• Compliant to RoHS directive 2002/95/EC

Halogen-free according to IEC 61249-2-21 definition

• Designed and qualified for industrial level

DESCRIPTION/APPLICATIONS

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop and hyperfast recovery time, and soft recovery.

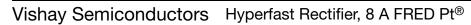
The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the ac-to-dc section of SMPS, inverters or as freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Peak repetitive reverse voltage	V_{RRM}		600	V	
Average rectified forward current	I _{F(AV)}	T _C = 133 °C	8		
FULL-PAK		T _C = 78 °C	0	Α	
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C	70	A	
Peak repetitive forward current	I _{FM}		16		
Operating junction and storage temperatures	T _J , T _{Stg}		- 65 to 175	°C	

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V _{BR} , V _R	Ι _R = 100 μΑ	600	-	-	
Forward voltage V _F	I _F = 8 A	-	2.1	2.5	V	
	I _F = 8 A, T _J = 150 °C	-	1.6	1.9		
Reverse leakage current I _R		V _R = V _R rated	-	0.2	35	
		T _J = 150 °C, V _R = V _R rated	-	50	350	μA
Junction capacitance	C _T	V _R = 600 V	-	6	-	pF
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8	-	nH





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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
		$I_F = 1.0 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	17	23	
		$I_F=8.0~A,~dI_F/dt=100~A/\mu s,~V_R=30~V$		ı	22	25	
		T _J = 25 °C	$I_F = 8 A$ $dI_F/dt = 200 A/\mu s$	ı	22	ı	
Reverse recovery time	t _{rr}		$V_{R} = 390 \text{ V}$	ı	43	ı	ns
		T _J = 125 °C	$I_F = 8 \text{ A}$ $dI_F/dt = 600 \text{ A/}\mu\text{s}$ $V_R = 390 \text{ V}$	-	33	-	
	l==	T _J = 25 °C	I _F = 8 A dI _F /dt = 200 A/µs	-	3.1	-	A
Peak recovery current		I _{RRM} T _J = 125 °C	$V_{R} = 390 \text{ V}$	-	5.2	-	
reactecovery current IRRM	чкм		I _F = 8 A dI _F /dt = 600 A/μs V _R = 390 V	ı	13	ı	
Reverse recovery charge	Q _{rr}	T _J = 25 °C	I _F = 8 A	-	32	-	
		T _J = 125 °C	$dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 390 \text{ V}$	-	120	-	nC
			I _F = 8 A dI _F /dt = 600 A/μs V _R = 390 V	-	230	-	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		- 65	-	175	°C
Thermal resistance,	D		-	2	2.4	
junction to case FULL-PAK	R_{thJC}		-	5	5.5	
Thermal resistance, junction to ambient per leg	R _{thJA}	Typical socket mount	-	-	70	°C/W
Typical thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-	
Weight			-	2	-	g
Weight			-	0.07	-	OZ.
Mounting torque			6 (5)	-	12 (10)	kgf · cm (lbf · in)
Modeing doving		Case style TO-220	8E2TH06			
Marking device		Case style TO-220 FULL-PAK	8E2TH06FP			





Hyperfast Rectifier, 8 A FRED Pt® Vishay Semiconductors

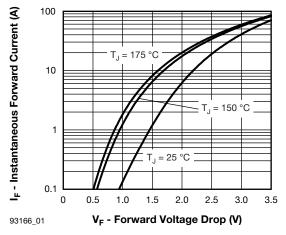


Fig. 1 - Typical Forward Voltage Drop Characteristics

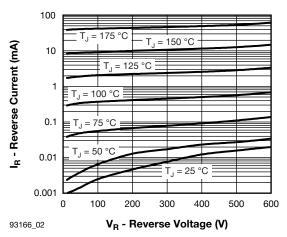


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

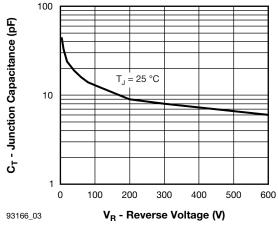


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

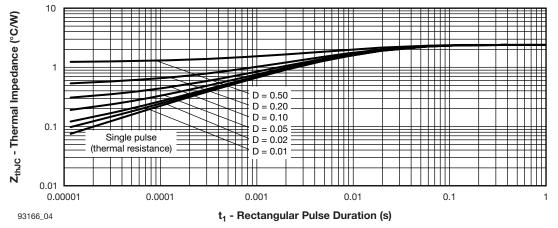


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics (TO-220)

Vishay Semiconductors Hyperfast Rectifier, 8 A FRED Pt®



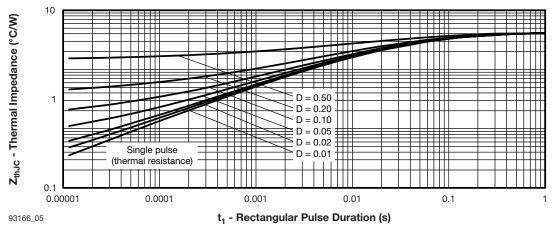


Fig. 5 - Maximum Thermal Impedance Z_{thJC} Characteristics (FULL-PAK)

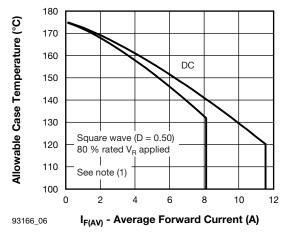


Fig. 6 - Maximum Allowable Case Temperature vs. Average Forward Current (TO-220)

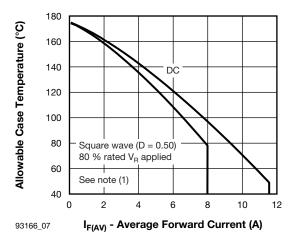


Fig. 7 - Maximum Allowable Case Temperature vs. Average Forward Current (FULL-PAK)

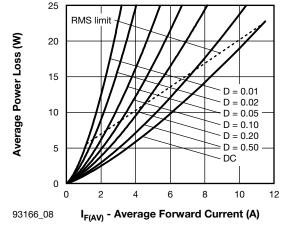


Fig. 8 - Forward Power Loss Characteristics

Note

 $^{(1)} \ \ Formula \ used: T_C = T_J - (Pd + Pd_{REV}) \ x \ R_{thJC}; Pd = Forward \ power \ loss = I_{F(AV)} \ x \ V_{FM} \ at \ (I_{F(AV)}/D) \ (see \ fig. \ 6); \\ Pd_{REV} = Inverse \ power \ loss = V_{R1} \ x \ I_R \ (1 - D); \ I_R \ at \ V_{R1} = Rated \ V_R$

Hyperfast Rectifier, 8 A FRED Pt® Vishay Semiconductors

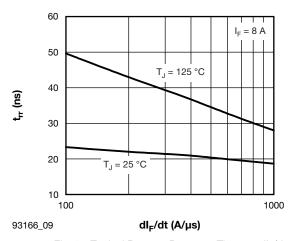


Fig. 9 - Typical Reverse Recovery Time vs. dI_F/dt

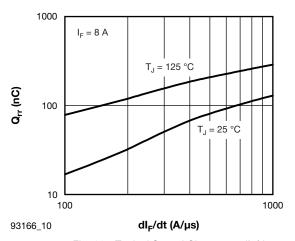


Fig. 10 - Typical Stored Charge vs. dl_F/dt

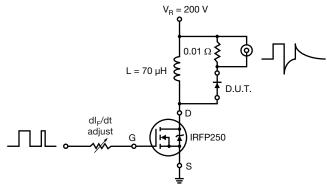
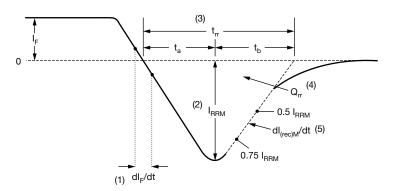


Fig. 11 - Reverse Recovery Parameter Test Circuit



- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_F$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) $\mathbf{Q}_{\rm rr}$ area under curve defined by $\mathbf{t}_{\rm rr}$ and $\mathbf{I}_{\rm RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) dl_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

Fig. 12 - Reverse Recovery Waveform and Definitions

Vishay Semiconductors Hyperfast Rectifier, 8 A FRED Pt®

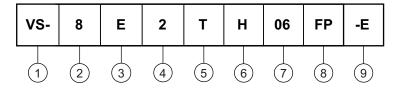


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ORDERING INFORMATION TABLE

Device code



- Vishay Semiconductors product suffix
- 2 Current rating (8 = 8 A)
- 3 Circuit configuration:
 - E = Single diode
- 4 2 = True 2 pin package
- **5** T = TO-220
- 6 H = Hyperfast recovery time
- 7 Voltage code (06 = 600 V)
- 8 None = TO-220
 - FP = FULL-PAK
- 9 Environmental digit:
 - -E = RoHS compliant and terminations lead (Pb)-free
 - -M = Halogen-free, RoHS compliant and terminations lead (Pb)-free

ORDERING INFORMATION (Example)					
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION		
VS-8E2TH06-E	50	1000	Antistatic plastic tubes		
VS-8E2TH06-M	50	1000	Antistatic plastic tubes		
VS-8E2TH06FP-E	50	1000	Antistatic plastic tubes		

LINKS TO RELATED DOCUMENTS				
Dimensions TO-220AC		www.vishay.com/doc?95259		
Differisions	TO-220 FULL-PAK	www.vishay.com/doc?95260		
Part marking information	TO-220AC	www.vishay.com/doc?95391		
Fait marking information	TO-220 FULL-PAK	www.vishay.com/doc?95392		
Packaging information		www.vishay.com/doc?95388		





Vishay

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